# **2SC3707** Silicon NPN epitaxial planar type

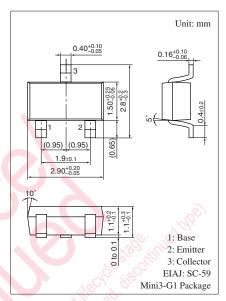
For UHF amplification

#### Features

- Possible with the small current and low voltage
- $\bullet$  High transition frequency  $f_{\rm T}$
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing

#### Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	10	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	7	V	
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	2	V	
Collector current	I <sub>C</sub>	10	mA	
Collector power dissipation	P <sub>C</sub>	50	mW	
Junction temperature	Tj	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C	

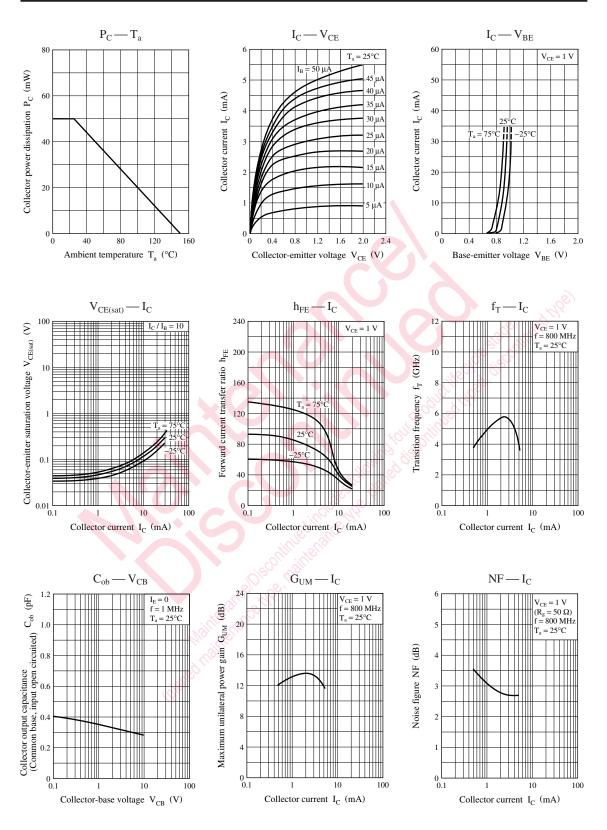


#### Marking Symbol: 2X

### Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = 10 \text{ V}, I_E = 0$			1	μΑ
Emitter-base cutoff current (Collector open)	I <sub>EBO</sub>	$V_{EB} = 1.5 V, I_C = 0$			1	μΑ
Forward current transfer ratio	h <sub>FE</sub>	$V_{CE} = 1 V, I_C = 1 mA$	50		150	—
Transition frequency	f <sub>T</sub>	$V_{CE} = 1 \text{ V}, \text{ I}_{C} = 1 \text{ mA}, \text{ f} = 0.8 \text{ GHz}$		4		GHz
Collector output capacitance (Common base, input open circuited)	C <sub>ob</sub>	$V_{CB} = 1 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		0.4		pF
Forward transfer gain	S <sub>21e</sub> 2	$V_{CE} = 1 V, I_C = 1 mA, f = 0.8 GHz$		6.0		dB
Maximum unilateral power gain	G <sub>UM</sub>	$V_{CE} = 1 \text{ V}, I_C = 1 \text{ mA}, f = 0.8 \text{ GHz}$		15		dB
Noise figure	NF	$V_{CE} = 1 V, I_C = 1 mA, f = 0.8 GHz$		3.5		dB

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.2. Handle the product with care because this is sensitive to the electrostatic breakdown by its structure



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